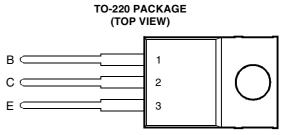
## BD646, BD648, BD650, BD652 PNP SILICON POWER DARLINGTONS

# BOURNS®

- Designed for Complementary Use with BD645, BD647, BD649 and BD651
- 62.5 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Minimum h<sub>FE</sub> of 750 at 3V, 3 A



Pin 2 is in electrical contact with the mounting base.

#### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	BD646		-80		
Collector-base voltage ( $I_E = 0$ )	BD648	V	-100	v	
	BD650	V <sub>CBO</sub>	-120	v	
	BD652		-140		
Collector-emitter voltage (I <sub>B</sub> = 0)	BD646		-60		
	BD648	V	-80	v	
	BD650	V <sub>CEO</sub>	-100		
	BD652		-120		
Emitter-base voltage			-5	V	
Continuous collector current			-8	Α	
Peak collector current (see Note 1)			-12	A	
Continuous base current			-0.3	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			62.5	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P <sub>tot</sub>	2	W	
Unclamped inductive load energy (see Note 4)			50	mJ	
Operating junction temperature range			-65 to +150	°C	
Storage temperature range			-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds			260	°C	

NOTES: 1. This value applies for  $t_p \leq 0.3$  ms, duty cycle  $\leq 10\%.$ 

2. Derate linearly to 150°C case temperature at the rate of 0.4 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH,  $I_{B(on)}$  = -5 mA,  $R_{BE}$  = 100  $\Omega$ ,  $V_{BE(off)}$  = 0,  $R_S$  = 0.1  $\Omega$ ,  $V_{CC}$  = -20 V.

### PRODUCT INFORMATION

# BD646, BD648, BD650, BD652 PNP SILICON POWER DARLINGTONS



#### electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER		TEST C	ONDITIONS		MIN	ТҮР	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> = -30 mA	I <sub>B</sub> = 0	(see Note 5)	BD646 BD648	-60 -80			
					BD650	-100			V
					BD652	-120			
I <sub>CEO</sub>	Collector-emitter cut-off current	V <sub>CE</sub> = -30 V	I <sub>B</sub> = 0		BD646			-0.5	
		$V_{CE} = -40 V$	$I_B = 0$		BD648			-0.5	mA
		V <sub>CE</sub> = -50 V	I <sub>B</sub> = 0		BD650			-0.5	
		V <sub>CE</sub> = -60 V			BD652			-0.5	
Сво	Collector cut-off current	V <sub>CB</sub> = -60 V	-		BD646			-0.2	
		V <sub>CB</sub> = -80 V	$I_E = 0$		BD648			-0.2	
		V <sub>CB</sub> = -100 V	$I_E = 0$		BD650			-0.2	
		V <sub>CB</sub> = -120 V	-		BD652			-0.2	mA
		V <sub>CB</sub> = -40 V		T <sub>C</sub> = 150°C	BD646			-2.0	
		V <sub>CB</sub> = -50 V		$T_{C} = 150^{\circ}C$	BD648			-2.0	
		V <sub>CB</sub> = -60 V		$T_{C} = 150^{\circ}C$	BD650			-2.0	
		V <sub>CB</sub> = -70 V	$I_E = 0$	$T_{C} = 150^{\circ}C$	BD652			-2.0	
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> = -5 V	$I_{\rm C} = 0$	(see Notes 5 and 6)				-5	mA
h <sub>FE</sub>	Forward current transfer ratio	V <sub>CE</sub> = -3 V	l <sub>C</sub> = -3 A	(see Notes 5 and 6)		750			
V <sub>CE(sat)</sub>	Collector-emitter	I <sub>B</sub> = -12 mA	I <sub>C</sub> = -3 A	(see Notes 5 and 6)				-2	V
	saturation voltage	I <sub>B</sub> = -50 mA	I <sub>C</sub> = -5 A	(SEE NOLES 5 ANU 0)				-2.5	v
V <sub>BE(sat)</sub>	Base-emitter	ln = -50 mA	I <sub>C</sub> = -5 A	(see Notes 5 and 6)	16)			-3	V
	saturation voltage	- 00 mA			,			Ŭ	v
V <sub>BE(on)</sub>	Base-emitter voltage	V <sub>CE</sub> = -3 V	I <sub>C</sub> = -3 A	(see Notes 5 and	16)			-2.5	V

NOTES: 5. These parameters must be measured using pulse techniques,  $t_p = 300 \ \mu s$ , duty cycle  $\leq 2\%$ .

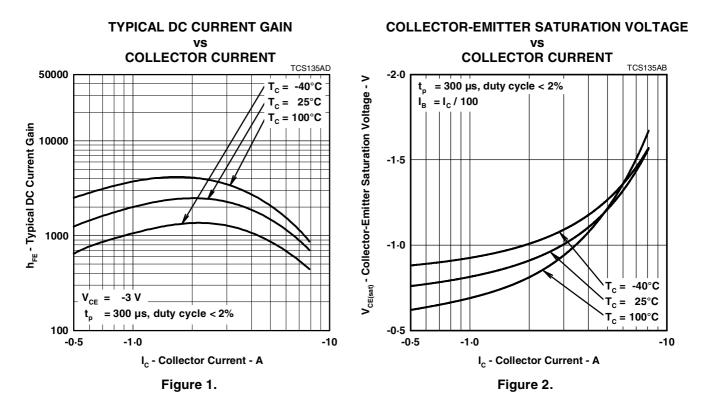
6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

#### thermal characteristics

PARAMETER		MIN	ТҮР	MAX	UNIT
$R_{ extsf{ heta}JC}$	Junction to case thermal resistance			2.0	°C/W
$R_{\thetaJA}$	Junction to free air thermal resistance			62.5	°C/W



### **TYPICAL CHARACTERISTICS**

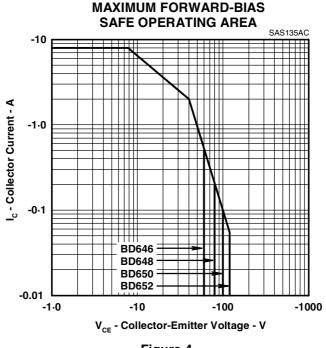


**BASE-EMITTER SATURATION VOLTAGE** vs **COLLECTOR CURRENT** TCS135AC -3.0 -40°C = V<sub>BE(sat)</sub> - Base-Emitter Saturation Voltage - V тс 25°C T<sub>c</sub> = = 100°C -2.5 -2.0 -1.5 -1.0 = I<sub>c</sub> / 100 I<sub>R</sub> = 300  $\mu$ s, duty cycle < 2% -0.5 -0.5 -1.0 -10 I<sub>c</sub> - Collector Current - A Figure 3.

#### PRODUCT INFORMATION

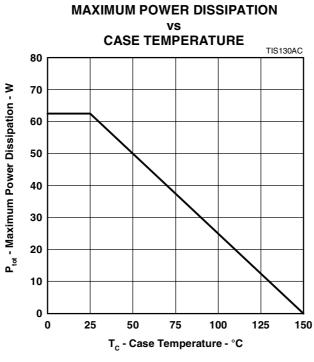
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#### MAXIMUM SAFE OPERATING REGIONS











PRODUCT INFORMATION

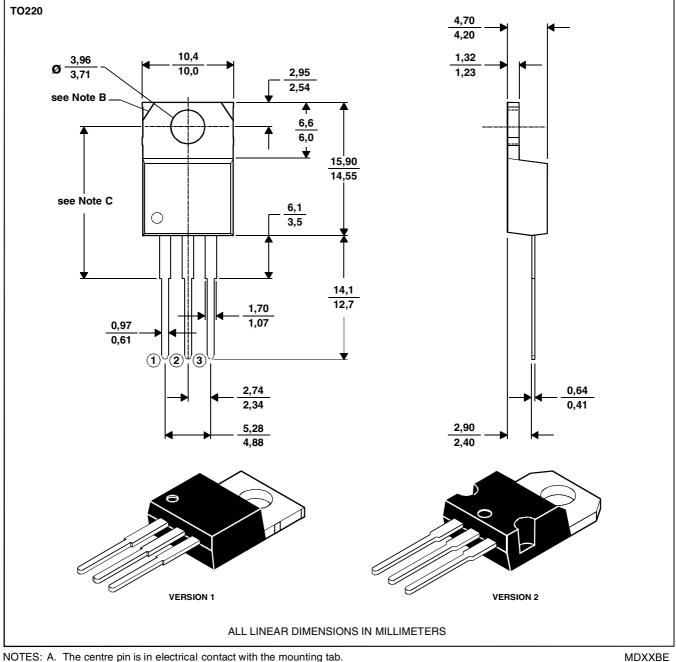
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#### **MECHANICAL DATA**

#### **TO-220**

#### 3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



B. Mounting tab corner profile according to package version.

C. Typical fixing hole centre stand off height according to package version. Version 1, 18.0 mm. Version 2, 17.6 mm.

#### PRODUCT INFORMATION

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